**Product data sheet** 

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006-3 (SOT883) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- Leadless ultra small and ultra thin SMD plastic package

## 3. Applications

- Relay driver
- · High-speed line driver
- · Low-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	50	V
V <sub>GS</sub>	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	350	mA
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 4.5 V; $I_D$ = 200 mA; $T_j$ = 25 °C		-	2	2.8	Ω

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.



50 V, N-channel Trench MOSFET

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1 🔲	D
2	S	source	2 3	
3	D	drain	Transparent top view DFN1006-3 (SOT883)	G S 017aaa255

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package						
	Name	Description	Version				
NX5008NBKM	DFN1006-3	plastic, leadless ultra small package; 3 terminals; 0.35 mm pitch; 1 mm x 0.6 mm x 0.48 mm body	SOT883				

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
NX5008NBKM	Y3

50 V, N-channel Trench MOSFET

## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	50	V
V <sub>GS</sub>	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	350	mA
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	220	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	1.45	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	350	mW
			[1]	-	700	mW
		T <sub>sp</sub> = 25 °C		-	2.8	W
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-draii	n diode					
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	350	mA

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

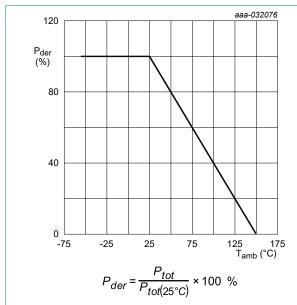


Fig. 1. Normalized total power dissipation as a function of ambient temperature

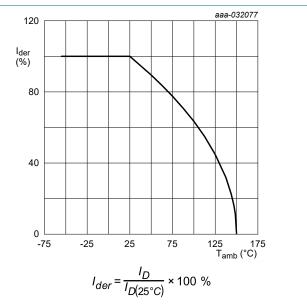


Fig. 2. Normalized continuous drain current as a function of ambient temperature

#### 50 V, N-channel Trench MOSFET

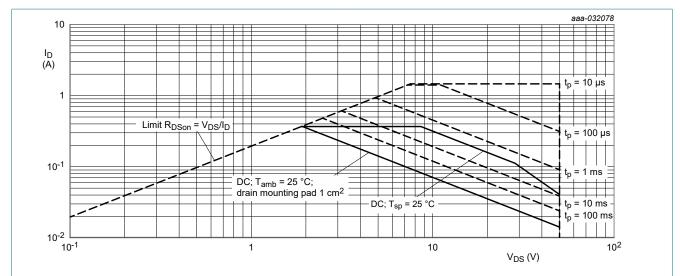


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

50 V, N-channel Trench MOSFET

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	[1]	-	314	360	K/W
	junction to ambient		[2]	-	159	180	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	35	40	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.

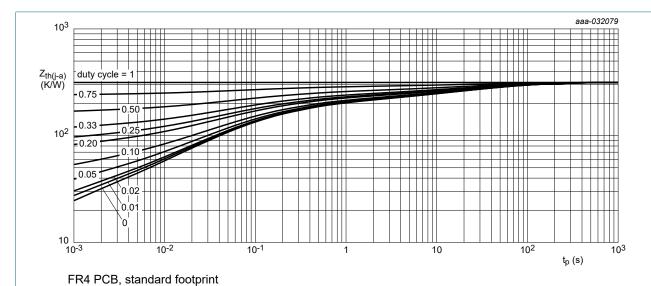
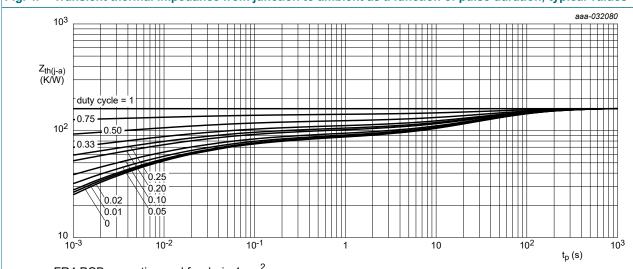


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm<sup>2</sup>

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

50 V, N-channel Trench MOSFET

## 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	50	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	0.4	0.7	0.9	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μΑ
		V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μΑ
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
		V <sub>GS</sub> = -4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μΑ
		V <sub>GS</sub> = 2.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		V <sub>GS</sub> = -2.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 25 °C	-	2	2.8	Ω
	resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 150 °C	-	4.3	6	Ω
		V <sub>GS</sub> = 2.5 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 25 °C	-	2.1	3	Ω
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; $I_{D}$ = 200 mA; $T_{j}$ = 25 °C	-	1.1	-	S
Dynamic ch	naracteristics		l			
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 25 V; I <sub>D</sub> = 200 mA; V <sub>GS</sub> = 4.5 V;	-	0.47	0.7	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.04	-	nC
$Q_{GD}$	gate-drain charge		-	0.1	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 25 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	29	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	2.9	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	2	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 25 V; I <sub>D</sub> = 200 mA; V <sub>GS</sub> = 4.5 V;	-	3	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	4	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	17	-	ns
t <sub>f</sub>	fall time	1	-	3	-	ns
Source-dra	in diode		,			
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 350 mA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	0.9	1.2	V

### 50 V, N-channel Trench MOSFET

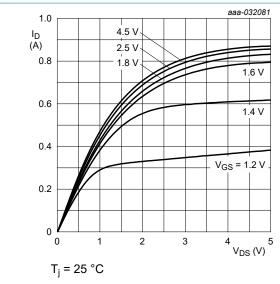


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

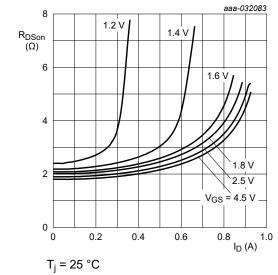


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

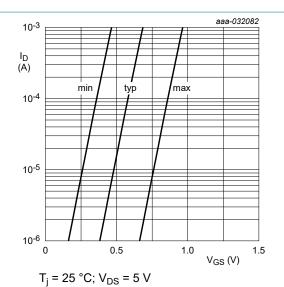


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

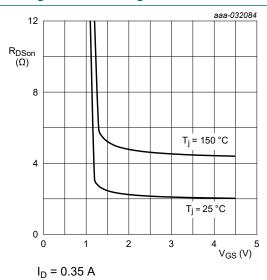


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### 50 V, N-channel Trench MOSFET

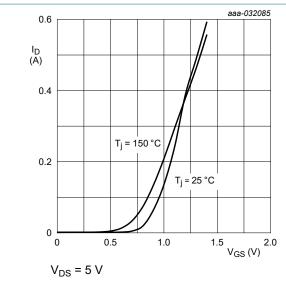


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

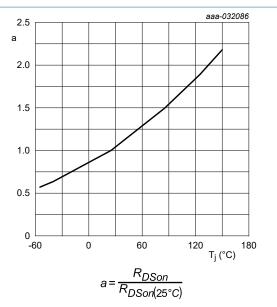


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

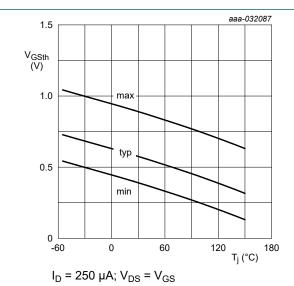
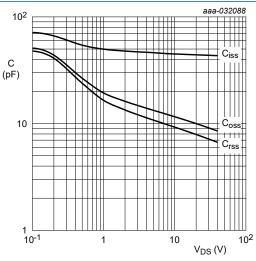


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

#### 50 V, N-channel Trench MOSFET

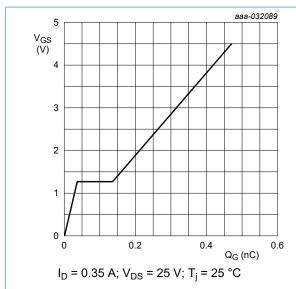


Fig. 14. Gate-source voltage as a function of gate charge; typical values

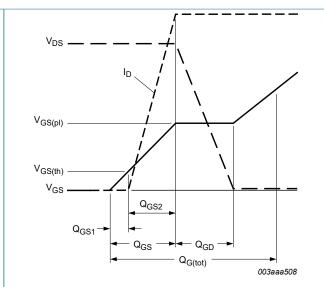


Fig. 15. Gate charge waveform definitions

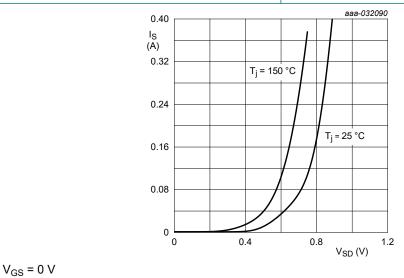
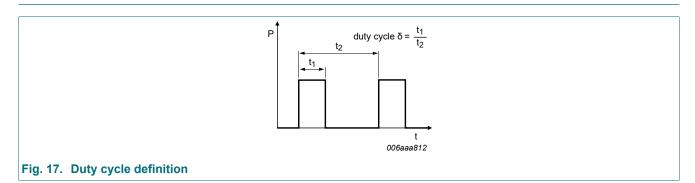


Fig. 16. Source current as a function of source-drain voltage; typical values

### 11. Test information



50 V, N-channel Trench MOSFET

# 12. Package outline

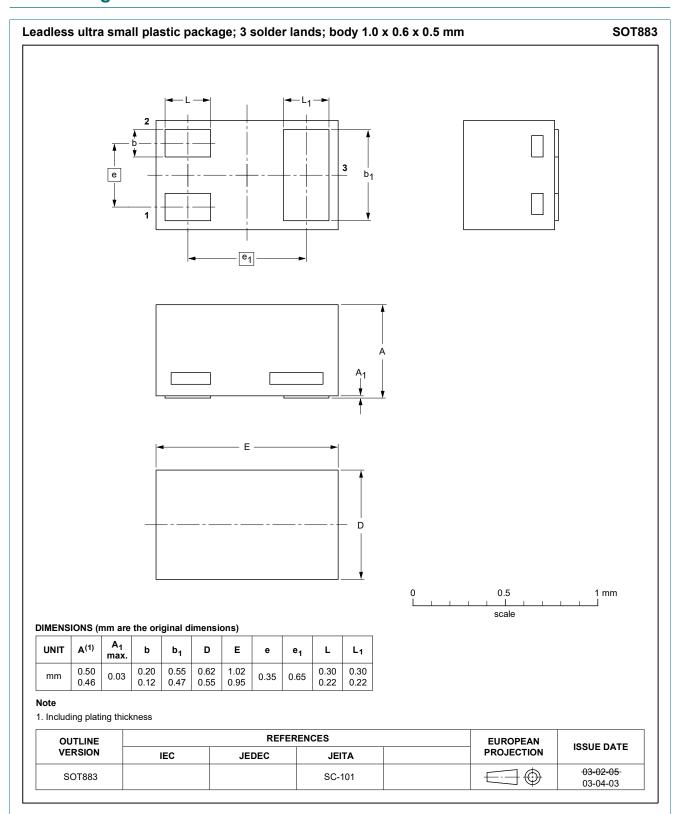
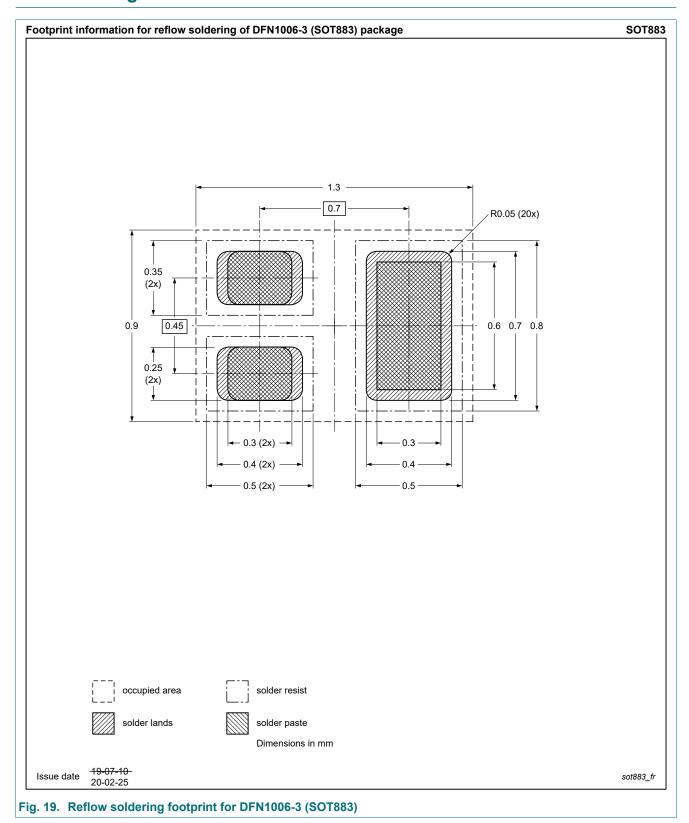


Fig. 18. Package outline DFN1006-3 (SOT883)

50 V, N-channel Trench MOSFET

## 13. Soldering



50 V, N-channel Trench MOSFET

# 14. Revision history

#### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
NX5008NBKM v.1	20200901	Product data sheet	-	-

#### 50 V, N-channel Trench MOSFET

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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### 50 V, N-channel Trench MOSFET

## **Contents**

General description	. 1
Features and benefits	1
Applications	1
Quick reference data	. 1
Pinning information	. 2
Ordering information	. 2
Marking	. 2
Limiting values	3
Thermal characteristics	5
Characteristics	. 6
Test information	. 9
Package outline1	10
Soldering 1	11
Revision history1	12
Legal information1	
	Features and benefits

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